

CentralTM Semiconductor Corp.

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Manufacturers of World Class Discrete Semiconductors

CMPF5460
CMPF5461
CMPF5462

SURFACE MOUNT
SILICON P-CHANNEL JFET

SOT-23 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPF5460 Series types are epoxy molded P-Channel Silicon Junction Field Effect Transistor manufactured in an SOT-23 case, designed for low level amplifier applications.

Marking code is 6E, 6E1 and 6E2 respectively.

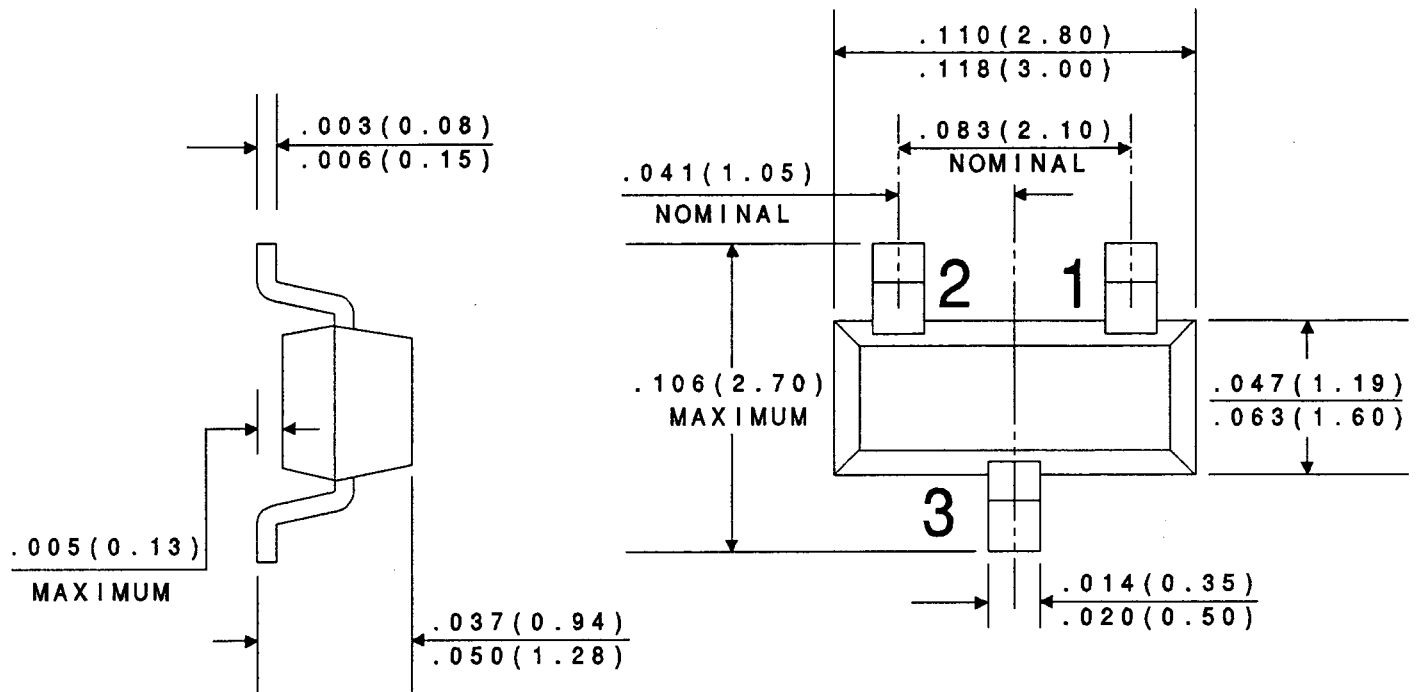
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Gate-Drain Voltage	V _{GD}	40	V
Gate-Source Voltage	V _{GS}	40	V
Gate Current	I _G	10	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPF5460		CMPF5461		CMPF5462		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
I _{GSS}	V _{GS} =20V		5.0		5.0		5.0	nA
I _{DSS}	V _{DS} =15V	1.0	5.0	2.0	9.0	4.0	16	mA
BV _{GSS}	I _G =10μA	40		40		40		V
V _{GS(off)}	V _{DS} =15V, I _D =1.0nA	0.75	6.0	1.0	7.5	1.8	9.0	V
g _{fs}	V _{DS} =15V, V _{GS} =0, f=1.0kHz	1.0	5.0	1.5	5.5	2.0	6.0	μmhos
C _{iss}	V _{DS} =15V, V _{GS} =0, f=1.0MHz		7.0		7.0		7.0	pF
C _{rss}	V _{DS} =15V, V _{GS} =0, f=1.0MHz		3.0		3.0		3.0	pF
e _N	V _{DS} =15V, V _{GS} =0, f=100Hz	60 TYP.		60 TYP.		60 TYP.		nV/√Hz

SOT-23 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm)

LEAD CODE:

- 1) DRAIN
- 2) SOURCE
- 3) GATE

MARKING CODE:

CMPF5460 - 6E
CMPF5461 - 6E1
CMPF5462 - 6E2